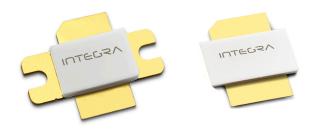


S-Band, GaN/SiC, RF Power Transistor

2.7 - 2.9 GHz | 2000W | 55 % Efficiency typ | 14 dB Gain typ | 100 V | 100μs Pulse Length, 10% Duty Cycle

IGN2729M1700 and IGN2729M1700S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of modern radar systems. They supply a minimum of 1700W of peak output power, with typically 14 dB of associated gain and 50% efficiency. They operate from a 100V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >1700W
- Pre-matched Input and Output Impedances
- High Efficiency up to 55%
- 100% RF Tested under 100μs, 10% duty cycle pulse conditions
- RoHS and REACH Compliant

APPLICATIONS

S-band Radar Systems

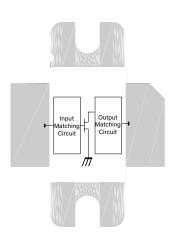


Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Gain	G		14		dB	
Drain Efficiency	η		50		%	P _{out} = 1700W
Pulse Droop	D		-0.45		dB	f = 2.7, 2.8, 2.9 GHz
Input Return Loss	IRL		15		dB	
VSWR Mismatch Stability	VSWR-S	2:1				100μs pulse length, 10% duty cycle $V_{DS} = 100V, I_{DS} = 75mA$
VSWR Withstand	VSWR-LMT	5:1				0 _{DS} = 100 0, 1 _{DS} = 1011111

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.



Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V _{DS}	350	V	25 ºC
DC Gate-Source Voltage	V _{GS}	-8 to +1	V	25 °C
DC Drain Current	I _D	72	А	25 °C
DC Gate Current	I _G	14.4	mA	25 °C
RF Input Power	P _{RE,IN}	135	W	25 °C
Operating Channel Temperature	Т _{сн}	-55 to +225	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	
Soldering Temperature	T _{SOLDER}	260 for 60s	°C	

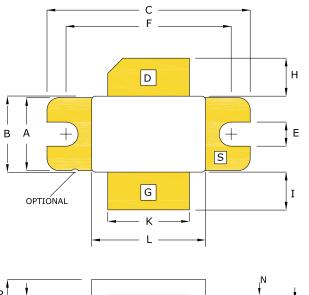
Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V _P	-5.0			V	$V_{DS} = 100V, I_{DS} = 1mA$
Quiescent Gate Voltage	V _Q		-4.0		V	V _{DS} = 100V, I _{DS} = 75mA



PACKAGE PL64B1

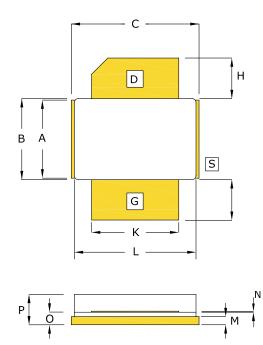


	INCHES	S	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.380	0.390	9.65	9.91
В	0.395	0.405	10.03	10.29
С	1.065	1.075	27.05	27.31
E	0.123	0.133	3.12	3.38
F	0.865	0.875	21.97	22.23
Н	0.180	0.220	4.57	5.59
I	0.180	0.220	4.57	5.59
J				
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
М	0.035	0.045	0.89	1.14
N	0.004	0.006	0.10	0.15
	0.057	0.067	1.45	1.70
Р	0.142	0.175	3.61	4.45

	PIN S	SCHEDULE
	D	DRAIN
	S	SOURCE
ı	G	GATE



BOLT-DOWN FLANGE OPTION IGN2729M1700



	INCHES	3	MILLIM	1ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.380	0.390	9,65	9,91
В	0.395	0.405	10.03	10.29
С	0.625	0.635	15,88	16.13
E				
F				
Н	0.180	0.220	4.57	5.59
I	0.180	0.220	4.57	5.59
J			-	
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
М	0.035	0.045	0.89	1.14
N	0.004	0.006	0.10	0.15
	0.057	0.067	1.45	1.70
Р	0.142	0.175	3,61	4.45

PIN SCHEDULE				
D	DRAIN			
S	SOURCE			
G	GATE			

EARLESS FLANGE OPTION IGN2729M1700S



ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C11F
Moisture Sensitivty Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

 $Integra\, Technologies\, supports\, EU\, Regulation\, number\, 1907/2006\, concerning\, the\, Registration, Evaluation, Authorization, and\, Restriction\, of\, Chemicals\, (REACH)\, as\, these\, apply\, to\, Integra\, semiconductor\, products,\, development\, tools,\, and\, shipping\, packaging.$

In support of the REACH regulation, Integra will:

- •Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- •Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- •Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

Disclaimer

Integra Technologies Inc. reserves the right to make changes without further notice to any products herein. Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale.

DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865